

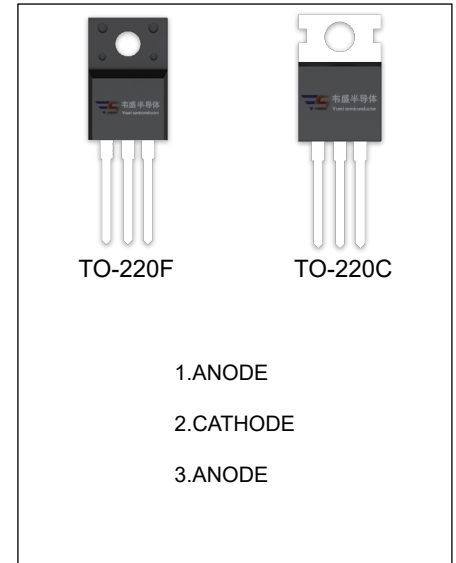
SBD10100TCTB、SBDF10100TCTB SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

I_O	10 (2×5) A
V_{RRM}	100 V
T_j	150 °C
$V_{F(typ)}$	0.63V (@$T_j=125^{\circ}C$)

FEATURES

- Low Power Loss,High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	SBD		Unit
		10100TCTB	F10100TCTB	
V_{RRM}	Peak repetitive reverse voltage	100		V
V_{RWM}	Working peak reverse voltage			
V_R	DC blocking voltage			
$V_{R(RMS)}$	RMS reverse voltage	70		V
I_O	Average rectified output current	10		A
I_{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)	150		A
$R_{\theta Jc}$	Thermal resistance from junction to case , $T_c=25^{\circ}C$	2.0	3.0	$^{\circ}C/W$
$R_{\theta JA}$	Thermal resistance from junction to ambient	62.5		$^{\circ}C/W$
T_j	Junction temperature	150		$^{\circ}C$
T_{stg}	Storage temperature	-55~+150		$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=0.1mA$	100			V
Reverse current	I_R	$V_R=100V$	$T_j=25^{\circ}C$	5.0	100	μA
			$T_j=125^{\circ}C$	5.0		mA
Forward voltage	V_F	$I_F=3A$	$T_j=25^{\circ}C$	0.58		V
			$T_j=125^{\circ}C$	0.55		V
		$I_F=5A$	$T_j=25^{\circ}C$	0.69	0.73	V
			$T_j=125^{\circ}C$	0.63		V

*Pulse test: pulse width $\leq 300\mu s$, duty cycles $\leq 2.0\%$.

FIG.1: FORWARD CURRENT DERATING CURVE

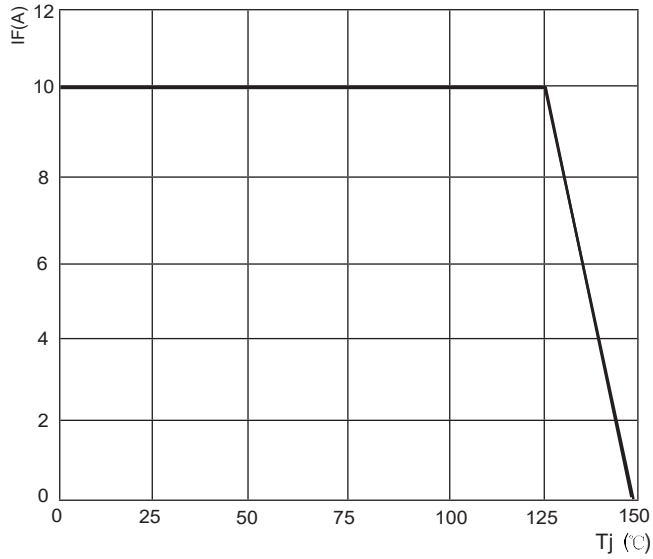


FIG.2: TYPICAL FORWARD CHARACTERISTICS

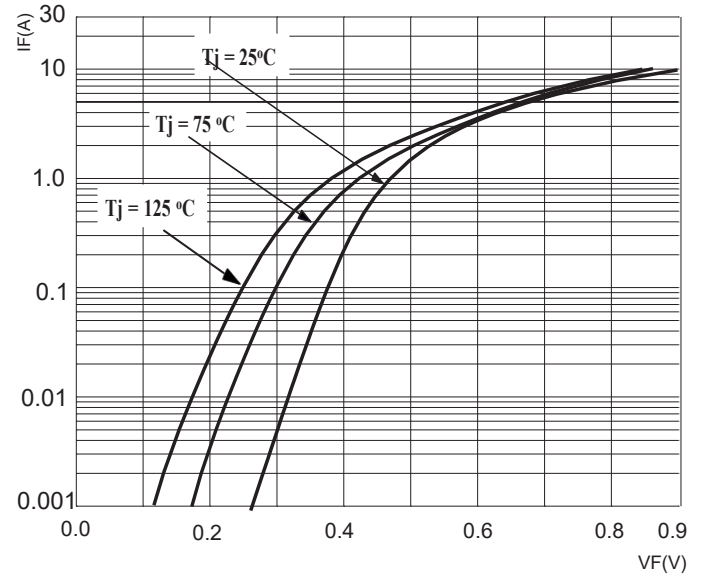


FIG.3: TOTAL CAPACITANCE DERATING CURVE

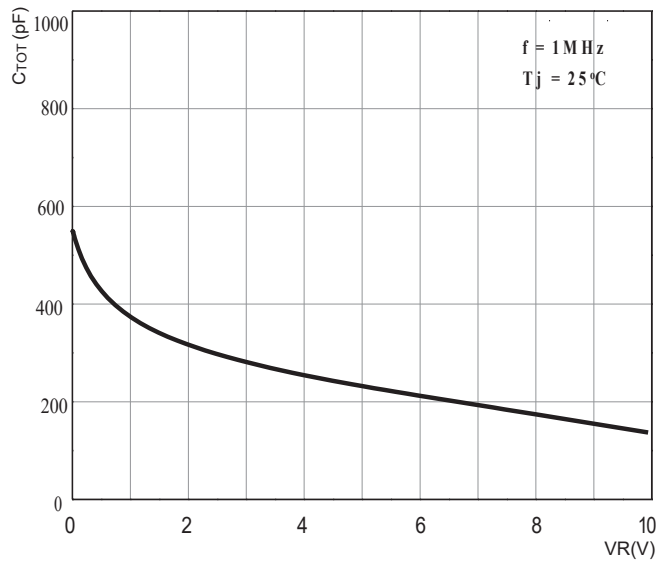


FIG.4: TYPICAL REVERSE CHARACTERISTICS

